



ELECTRONICS, INC.

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NTE2636 Silicon NPN Transistor Horizontal Deflection ^w/Internal Damper Diode

Features:

- High Breakdown Voltage: $V_{CES} = 1500V$
- Built-In Damper Diode
- Isolated TO3PFM Type Package

Applications:

- TV/Character Display Horizontal Deflection Output

Absolute Maximum Ratings: ($T_A = +25^\circ C$ unless otherwise specified)

Collector–Emitter Voltage, V_{CES}	1500V
Emitter–Base Voltage, V_{EBO}	6V
Collector Current, I_C	8A
Collector Peak Current, $I_{C(peak)}$	9A
Collector Surge Current, $I_{C(surge)}$	18A
Collector–Emitter Diode Forward Current, I_D	8A
Collector Power Dissipation ($T_C = +25^\circ C$), P_C	50W
Operating Junction Temperature, T_J	+150°C
Storage Temperature Range, T_{stg}	-55° to +150°C

Electrical Characteristics: ($T_A = +25^\circ C$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Emitter–Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = 500mA, I_C = 0$	6	–	–	V
Collector Cutoff Current	I_{CES}	$V_{CE} = 1500V, R_{BE} = 0$	–	–	500	μA
DC Current Transfer Ratio	h_{FE}	$V_{CE} = 5V, I_C = 1A$	–	–	25	
Collector–Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 6A, I_B = 1.2A$	–	–	5	V
Base–Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = 6A, I_B = 1.2A$	–	–	1.5	V
Collector–Emitter Diode Forward Voltage	V_{ECF}	$I_F = 8A$	–	–	2.0	V
Fall Time	t_f	$I_{CP} = 6A, I_{B1} = 1.2A, I_{B2} \cong -2.4A,$ $f_H = 31.5kHz$	–	–	0.5	μs

